TRANSISTOR (PNP)

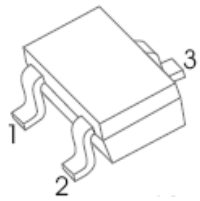
FEATURES

- Excellent h_{FE} Linearity
- Complementary to KTC4076

APPLICATIONS

- General Purpose Switching

SOT－323



1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	100	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	1250	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-35V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	70		240	
	$h_{FE(2)}$	V_{CE}=-6V, I_C=-400mA	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA			-0.25	V
Base-emitter voltage	V_{BE}	V_{CE}=-1V, I_C=-100mA			-1	V
Transition frequency	f_T	V_{CB}=-6V,I_C=-20mA ,		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-6V, I_E=0, f=1MHz		13		pF

CLASSIFICATION OF $h_{FE(1)}$, $h_{FE(2)}$

RANK	O(2)	Y(4)	O	Y
RANG $h_{FE(1)}$	70－140	120－240		
$h_{FE(2)}$			25Min	40Min
MARKING	ZO	ZY	ZO	ZY